

ABSTRACT OF THE DISCLOSURE

Provided are a semiconductor device having an etch stopper formed of a nitride film by low temperature atomic layer deposition which can prevent damage to a semiconductor substrate and a method for fabricating the semiconductor device.

5 Damage to the semiconductor substrate under the etch stopper composed of a second nitride film can be prevented by forming a first nitride film using high temperature LPCVD on the semiconductor substrate, forming the etch stopper including the second nitride film by low temperature ALD on the first nitride film, and removing the second nitride film by dry etching, thus taking advantage of the different etch selectivities of the first nitride film

10 and the second nitride film.

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